VS-P400 Series

Vishay Semiconductors

Power Modules, Passivated Assembled Circuit Elements, 40 A



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PACE-PAK (D-19)

PRIMARY CHARACTERISTICS					
Io	40 A				
Туре	Modules - thyristor, standard				
Package	PACE-PAK (D-19)				

FEATURES

- · Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 V_{RRM}/V_{DRM}
- High dynamic characteristics
- · Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved 😱
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-P400 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I _O	80 °C	40	А				
I _{TSM} ,	50 Hz	385	А				
I _{FSM}	60 Hz	400	A				
l ² t	50 Hz	745	A ² s				
1-1	60 Hz	680	A-5				
l²√t		7450	A²√s				
V _{RRM}	Range	400 to 1200	V				
V _{ISOL}		2500	V				
TJ		-40 to +125	°C				
T _{Stg}		-40 10 +125	U				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND PEAK OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J MAXIMUM mA			
VS-P401, VS-P421, VS-P431	400	500				
VS-P402, VS-P422, VS-P432	600	700				
VS-P403, VS-P423, VS-P433	P403, VS-P423, VS-P433 800		10			
VS-P404, VS-P424, VS-P434	1000	1100				
VS-P405, VS-P425, VS-P435	1200	1300				

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COMPLIANT





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PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum DC output current	1	Eull bridge	Full bridge circuits		40	А
at case temperature	I _O	Full bridge	circuits		80	°C
		t = 10 ms	No voltage		385	
Maximum peak, one-cycle	I _{TSM} ,	t = 8.3 ms	reapplied		400	^
non-repetitive on-state or forward current	I _{FSM}	t = 10 ms	100 % V _{BBM}		325	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	340	1
Maximum I ² t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	745	A ² s
	l ² t	t = 8.3 ms	reapplied	-	680	
		t = 10 ms	100 % V _{BBM}		530	
		t = 8.3 ms	reapplied		480	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied $l^{2}t$ for time tx = $l^{2}\sqrt{t} \cdot \sqrt{tx}$			7450	A²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	: x I _{T(AV)} < I < π x	$I_{T(AV)}$), $T_J = T_J$ maximum	0.83	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), TJ = TJ maxim	num	1.03	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	x I _{T(AV)} < I < π x	$I_{T(AV)}$), $T_J = T_J$ maximum	9.61	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		7.01	mΩ	
Maximum on-state voltage drop	V _{TM}	$I_{TM} = \pi \times I_{T(T)}$	(AV)	T _J = 25 °C	1.4	V
Maximum forward voltage drop	V _{FM}	$I_{FM} = \pi \times I_{F(AV)}$ $T_J = 25 \text{ °C}$		1.4	V	
Maximum non-repetitive rate of rise of turned-on current	dl/dt	$\begin{array}{l} T_{J} = 125 \ ^{\circ}C \ from \ 0.67 \ V_{DRM} \\ I_{TM} = \pi \ x \ I_{T(AV)}, \ I_{g} = 500 \ mA, \ t_{r} < 0.5 \ \mu s, \ t_{p} > 6 \ \mu s \end{array}$		200	A/µs	
Maximum holding current	Ι _Η	т об ос		GV registive lead	130	
Maximum latching current	١L	$T_J = 25$ °C anode supply = 6 V, resistive load		250	mA	

BLOCKING					
PARAMETER	SYMBOL TEST CONDITIONS VALUES				
Maximum critical rate of rise of off-state voltage	dV/dt	T_{J} = 125 °C, exponential to 0.67 V_{DRM} gate open	200	V/µs	
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM} , I _{DRM}	$I_1 = 125 \text{ G}$, gate open circuit		mA	
Maximum peak reverse leakage current	I _{RRM}	T _J = 25 °C	100	μA	
RMS isolation voltage	V _{ISOL}	V_{ISOL} 50 Hz, circuit to base, all terminals shorted, T _J = 25 °C, t = 1 s		V	

TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			8	W
Maximum average gate power	P _{G(AV)}			2	vv
Maximum peak gate current	I _{GM}			2	А
Maximum peak negative gate voltage	-V _{GM}			10	V
Maximum gate voltage required to trigger	V _{GT}	T _J = - 40 °C		3	V
		T _J = 25 °C	Anode supply =	2	
		T _J = 125 °C		1	
		T _J = - 40 °C	6 V resistive load	90	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C		60	mA
		T _J = 125 °C		35	
Maximum gate voltage that will not trigger	V _{GD}	$T_J = 125 \text{ °C}, \text{ rated } V_{DRM} \text{ applied}$ 0.2		0.2	V
Maximum gate current that will not trigger	I _{GD}			2	mA

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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case per junction	R _{thJC}	R _{thJC} DC operation		K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.10	r/ w
Mounting torque, base to heatsink ⁽¹⁾			4	Nm
Approximate weight			58	g
Approximate weight			2.0	oz.
Case style			PACE-PAK (D-19)	

Note

(1) A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

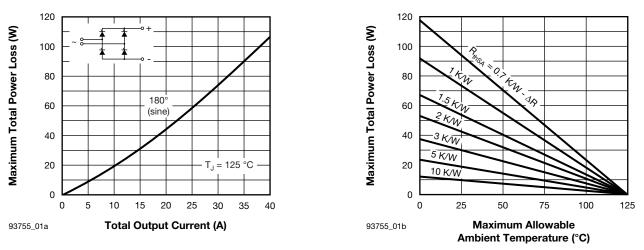
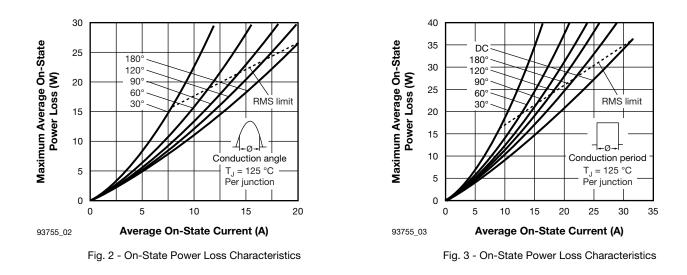


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)



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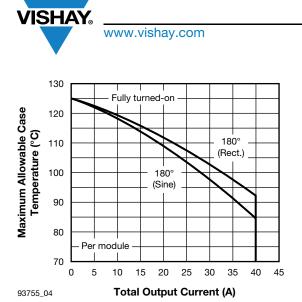


Fig. 4 - Current Ratings Characteristics

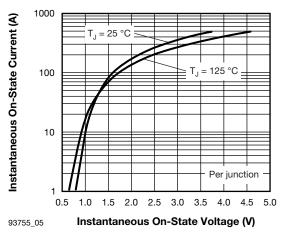


Fig. 5 - On-State Voltage Drop Characteristics

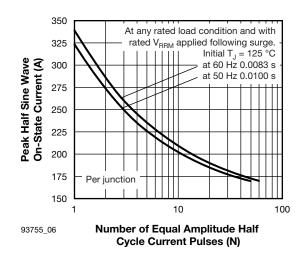
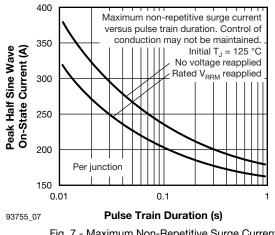
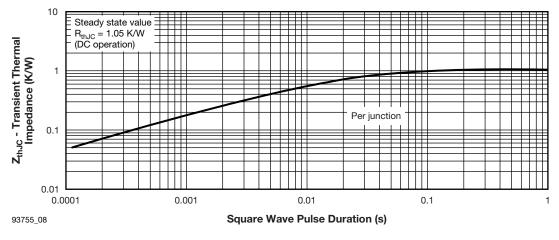
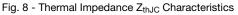


Fig. 6 - Maximum Non-Repetitive Surge Current









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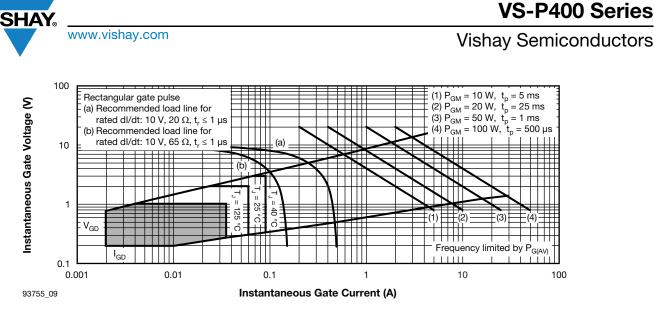


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	Р	4	0	2	к	w	
	1	2	3	4	5	6	7	
	1 2 3	- M - C 1 4	Vishay Semiconductors product Module type Current rating 1 = 25 A DC (P100 series) 4 = 40 A DC (P400 series) Circuit configuration					
		0 2	 0 = single phase, hybrid bridge common cathode 2 = single phase, hybrid bridge doubler connectio 3 = single phase, all SCR bridge 					
	5	1 2 3 4	bltage cod = 400 V = 600 V = 800 V = 1000 V = 1200 V					
	6	- K	= optiona	al voltag	e suppr	ession		
	7	- W	= option	al freew	heeling	diode		



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CIRCUIT CONFIGURATION				
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	SCHEMATIC DIAGRAM	TERMINAL POSITIONS	
Single phase, hybrid bridge common cathode	0	(-) $(-)$ $(+)$ $(+)$ $(+)$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	
Single phase, hybrid bridge doubler connection	2	$G1 \circ G2$ $AC2 \circ AC1 \circ O$ $(-) \circ O(+)$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	
Single phase, all SCR bridge	3	G^{3} G^{3} G^{1} AC_{2} G^{4} G^{2} $(+)$	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	

CODING ⁽¹⁾							
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	BASIC SERIES	WITH VOLTAGE SUPPRESSION	WITH FREEWHEELING DIODE	WITH BOTH VOLTAGE SUPPRESSION AND FREEWHEELING DIODE		
Single phase, hybrid bridge common cathode	0	P40.	P40.K	P40.W	P40.KW		
Single phase, hybrid bridge doubler connection	2	P42.	P42.K	-	-		
Single phase, all SCR bridge	3	P43.	P43.K	-	-		

Note

⁽¹⁾ To complete code refer to Voltage Ratings table, i.e.: for 600 V P40.W complete code is P402W

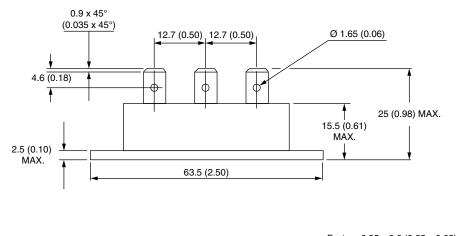
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95335			

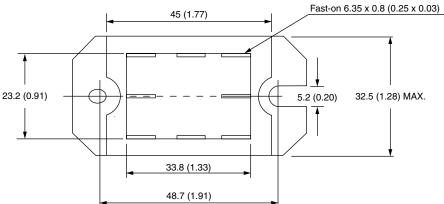
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D-19 PACE-PAK

DIMENSIONS in millimeters (inches)

SHAY







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